

KA1H0165RN/KA1H0165R

Fairchild Power Switch(FPS)

Features

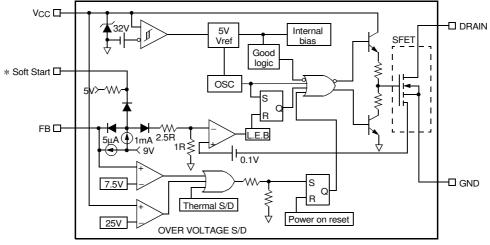
- Precision Fixed Operating Frequency (100kHz)
- Pulse by Pulse Over Current Limiting
- Over Load Protection
- Over Voltage Protection (Min. 23V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- · Auto Restart Mode

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit compared to discrete MOSFET and controller or RCC switching converter solution The Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.

8-DIP	TO-220F-4L
1 1.6.7.8. Drain 2. GND 3. VCC 4. F/B 5. S/S	1 1. GND 2. Drain 3. VCC 4. F/B

Internal Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Maximum Drain Voltage (1)	V _{D,MAX}	650	V
Drain-Gate Voltage (R _G S=1MΩ)	VDGR	650	V
Gate-Source (GND) Voltage	V _G S	±30	V
Drain Current Pulsed (2)	IDM	4.0	ADC
Single Pulsed Avalanche Energy (3)	Eas	95	mJ
Continuous Drain Current (T _C =25°C)	ID	1.0	ADC
Continuous Drain Current (Tc=100°C)	ID	0.7	ADC
Maximum Supply Voltage	VCC,MAX	30	V
Input Voltage Range	VFB	-0.3 to VSD	V
Total Power Dissipation	PD	40	W
	Darting	0.32	W/°C
Operating Ambient Temperature	TA	-25 to +85	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes:

- 1. $T_j = 25^{\circ}C$ to $150^{\circ}C$
- 2. Repetitive rating: Pulse width limited by maximum junction temperature 3. L = 80mH, VDD = 50V, RG = 27 Ω , starting Tj = 25°C

Electrical Characteristics (SFET Part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	VGS=0V, ID=50μA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
		V _{DS} =0.8Max., Rating, V _{GS} =0V, T _C =125°C	-	-	200	μΑ
Static Drain-Source on Resistance (Note)	RDS(ON)	V _{GS} =10V, I _D =0.5A	-	8	10	Ω
Forward Transconductance (Note)	gfs	V _{DS} =50V, I _D =0.5A	0.5	-	-	S
Input Capacitance	Ciss	V 0V V 05V	-	250	-	
Output Capacitance	Coss	VGS=0V, VDS=25V, f=1MHz	-	25	-	pF
Reverse Transfer Capacitance	Crss	1-11/11/2	-	10	-	
Turn on Delay Time	td(on)	V _{DD} =0.5B V _{DSS} , I _D =1.0A	-	12	-	
Rise Time	tr	(MOSFET switching	-	4	-	nS
Turn off Delay Time	td(off)	time is essentially independent of	-	30	-	113
Fall Time	tf	operating temperature)	-	10	-	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	V _G S=10V, I _D =1.0A, V _D S=0.5B V _D SS (MOSFET	-	-	21	
Gate-Source Charge	Qgs	switching time is essentially	-	3	-	nC
Gate-Drain (Miller) Charge	Qgd	independent of operating temperature)	-	9	-	

Note:

1. Pulse test: Pulse width $\leq 300 \mu S$, duty cycle $\leq 2\%$

$$2. S = \frac{1}{R}$$

Electrical Characteristics (Control Part) (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
UVLO SECTION							
Start Threshold Voltage	VSTART	-	14	15	16	V	
Stop Threshold Voltage	VSTOP	After turn on	9	10	11	V	
OSCILLATOR SECTION							
Initial Accuracy	Fosc	Ta=25°C	90	100	110	kHz	
Frequency Change With Temperature (2)	ΔΕ/ΔΤ	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%	
Maximum Duty Cycle	Dmax	-	64	67	70	%	
FEEDBACK SECTION							
Feedback Source Current	IFB	Ta=25°C, $0V \le Vfb \le 3V$	0.7	0.9	1.1	mA	
Shutdown Feedback Voltage	V _{SD}	-	6.9	7.5	8.1	V	
Shutdown Delay Current	Idelay	Ta=25°C, $5V \le Vfb \le V_{SD}$	4.0	5.0	6.0	μΑ	
SOFT START SECTION (KA1H0165RN)							
Soft Start Voltage	Vss	V _{FB} =2V	4.7	5.0	5.3	V	
Soft Start Current	ISS	Sync & S/S=GND	0.8	1.0	1.2	mA	
REFERENCE SECTION							
Output Voltage (1)	Vref	Ta=25°C	4.80	5.00	5.20	V	
Temperature Stability (1)(2)	Vref/∆T	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C	
CURRENT LIMIT(SELF-PROTECTION)SECTION							
Peak Current Limit	lover	Max. inductor current	0.53	0.6	0.67	Α	
PROTECTION SECTION							
Thermal Shutdown Temperature (1)	T _{SD}	-	140	160	-	°C	
Over Voltage Protection Voltage	VOVP	-	23	25	28	V	
TOTAL DEVICE SECTION							
Start-Up Current	ISTART	VCC=14V	0.1	0.3	0.4	mA	
Operating Supply Current (Control Part Only)	lop	Ta=25°C	6	12	18	mA	
V _{CC} Zener Voltage	Vz	ICC=20mA	30	32.5	35	V	

Note:

- 1. These parameters, although guaranteed, are not 100% tested in production
- 2. These parameters, although guaranteed, are tested in EDS (wafer test) process

Typical Performance Characteristics

(These characteristic graphs are normalized at Ta=25°C)

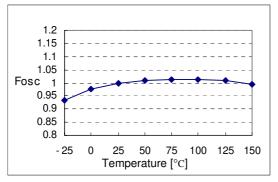


Figure 1. Operating Frequency

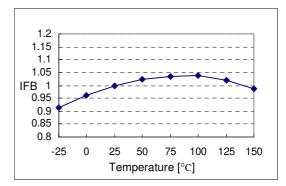


Figure 2. Feedback Source Current

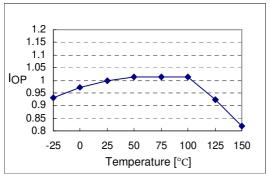


Figure 3. Operating Supply Current

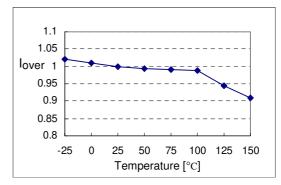


Figure 4. Peak Current Limit

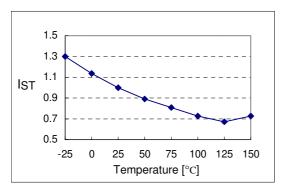


Figure 5. Start up Current

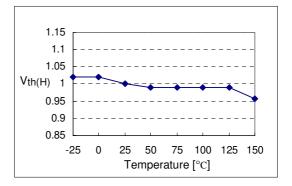


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at Ta=25°C)

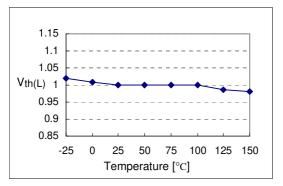


Figure 7. Stop Threshold Voltage

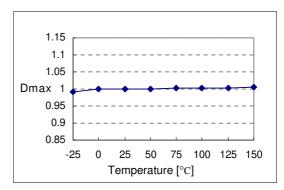


Figure 8. Maximum Duty Cycle

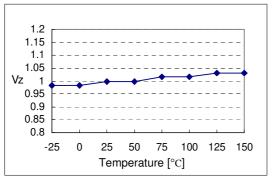


Figure 9. VCC Zener Voltage

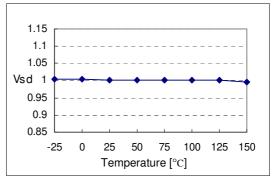


Figure 10. Shutdown Feedback Voltage

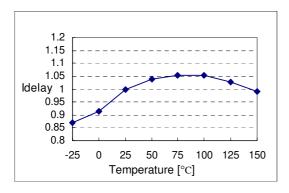


Figure 11. Shutdown Delay Current

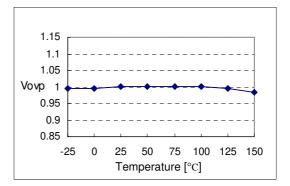


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic grahps are normalized at Ta=25°C)

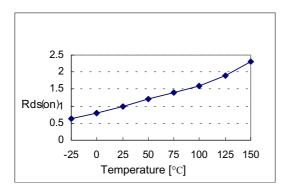
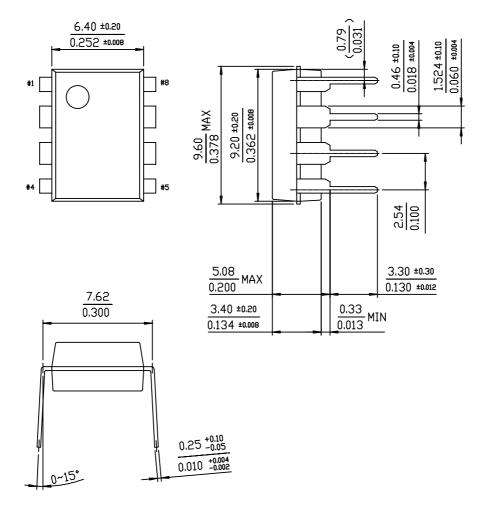


Figure 13. Static Drain-Source on Resistance

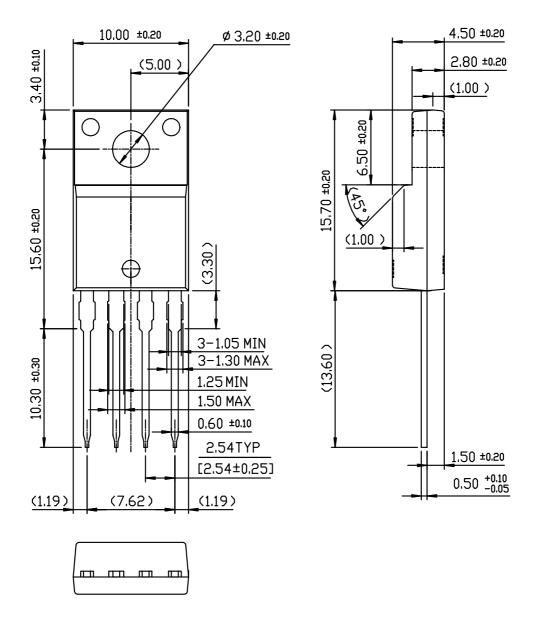
Package Dimensions

8-DIP



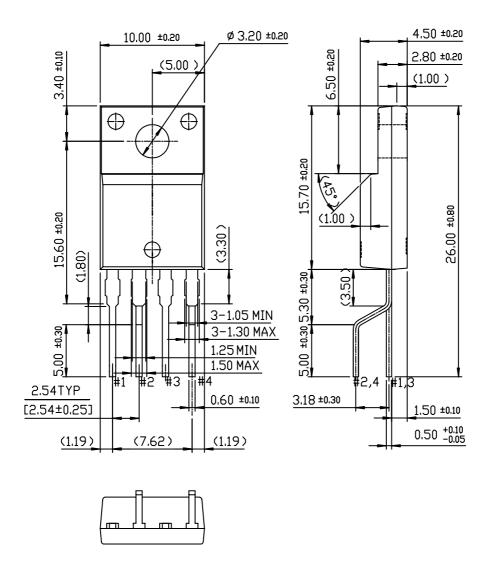
Package Dimensions (Continued)

TO-220F-4L



Package Dimensions (Continued)

TO-220F-4L(Forming)



Ordering Information

Product Number	Package	Rating	Operating Temperature
KA1H0165RN	8-DIP	650V, 1A	-25°C to +85°C
KA1H0165R-TU	TO-220F-4L	650V. 1A	-25°C to +85°C
KA1H0165R-YDTU	10-220F-4L	050V, 1A	-25 C to +65 C

TU : Non Forming Type YDTU : Forming Type

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